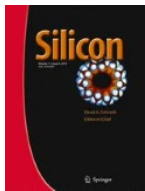


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Analog/RF Performance Analysis of a-ITZO Thin Film Transistor

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Abstract

This work reports RF and analog performance analysis of an amorphous Indium Tin Zinc Oxide thin film transistor. The various parameters affecting the performance of a-ITZO TFT like drain current, drain conductance, output resistance, transconductance, transconductance generation factor, early voltage, intrinsic gain, capacitances, cut off frequency, maximum frequency of oscillation, transconductance frequency product, gain frequency product, gain bandwidth product and gain transconductance frequency product have been closely examined. The device is further analyzed to investigate the impact of